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Approved for use 04-30-2003. OMB 0651-0031
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,044
Filing Dat	December 27, 2001
First Nam d Inv nt r	Ralph Johnson
Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02671 US

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Document Number Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
TN		US 4445218		04-24-1984	Coldren	
		US 4608697		08-26-1986	Coldren	
		US 4622672		11-11-1986	Coldren et al.	
		US 4829347		05-09-1989	Cheng et al.	
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		US 5045499		09-03-1991	Nishizawa et al.	
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		US 5245622	A	09-14-1993	Jewell et al.	
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		US 5392307	A	02-21-1995	Sugiyama et al.	
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		US 5693180	A	12-02-1997	Furukawa et al.	
		US 5719891	A	02-17-1998	Jewell	
TN		US 5719894	A	02-17-1998	Jewell et al.	

Examiner Signature	Tuan N Nguyen	Date Considered	5-20-03

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First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02671 US

TN		US	5719895	A	02-17-1998	Jewell et al.	
		US	5729567	A	03-17-1998	Nakagawa	
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First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02671 US

TN		US	6121068	A	09-19-2000	Ramdani et al.	
		US	6127200	A	10-03-2000	Ohiso et al.	
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TN		US	2003/0053510	A1	03-20-2003	Yuen et al.	

Examiner Signature	Tuan Nguyen	Date Considered	5-20-03

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COMPLETE IF KNOWN	
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First Named Inventor	Ralph Johnson
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Foreign Patent Document: Country Code[3]	Number[4]	Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T[6]
TN		EP	0 740 377	A1	10-30-1996	Hewlett-Packard Company		
		EP	0 740 377	B	10-30-1996	Hewlett-Packard Company		
		EP	0 765 014	A1	03-26-1997	France Telecom		
		EP	0 765 014	B1	07-28-1999	France Telecom		
		EP	0 822 630	A1	02-04-1998	Hewlett-Packard Company		
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		WO	01/017076	A2	03-08-2001	The Regents of the University of California		
TN		WO	01/017076	A3	03-08-2001	The Regents of the University of California		

Examiner Signature	Tuan Nguyen	Date Considered	5-20-03

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Sheet	5	Of	8

COMPLETE IF KNOWN	
Applicati n Number	10/026,044
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02671 US

TN		WO	01/018919	A1	03-15-2001	The Regents of the University of California	
		WO	01/024328	A2	04-05-2001	Agility Communications	
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TN		WO	02/084829	A1	10-24-2002	Cielo Communications, Inc.	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
TN		ALMUNEAU, G., et al., "Accurate control of Sb composition in AlGaAsSb alloys on InP substrates by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 208, 05-06-1999, pgs 113-6.	
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First Named Inventor	Ralph Johnson
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TN		KIM, J., et al., "Epitaxially-stacked multiple-active-region 1.55 μm lasers for increased differential efficiency", article, Applied Physics Letters, Vol 74, No 22, 05-31-1999, pgs 3251-3.	
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Examiner Signature	Tuan Nguyen	Date Considered	5-20-03

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COMPLETE IF KNOWN	
Applicati n Number	10/026,044
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02671 US

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Examiner Signature	Tuan N Nguyen	Date Considered	5-20-03

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